

N-channel 30 V 4.1 mΩ logic level MOSFET in D2PAK Rev. 1 — 22 March 2012 Product

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

Quick reference date

Table 1

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	30	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	1] -	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	103	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.9	5.8	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	3.5	4.1	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I _D = 15 A; V _{DS} = 15 V;	-	5	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15	-	19	-	nC
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	74	mJ

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			1 3 SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Orderin	g information		
Type number	Package		
	Name	Description	Version
PSMN4R3-30BL	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN4R3-30BL	PSMN4R3-30BL

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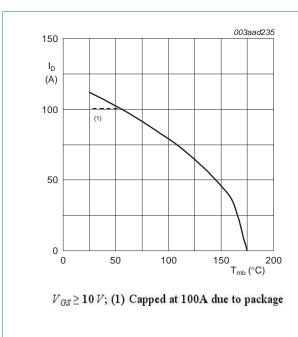
5. Limiting values

Table 5. Limiting values

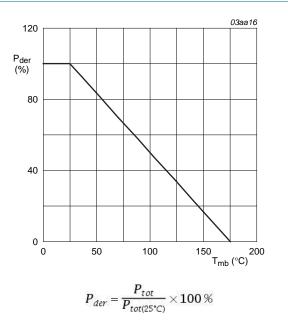
In accordance with the Absolute Maximum Rating System (IEC 60134).

		37 (7				
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	80	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 3</u>		-	465	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	103	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dra	ain diode					
I _S	source current	T _{mb} = 25 °C	<u>[1]</u>	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	465	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped		-	74	mJ

[1] Continuous current is limited by package.



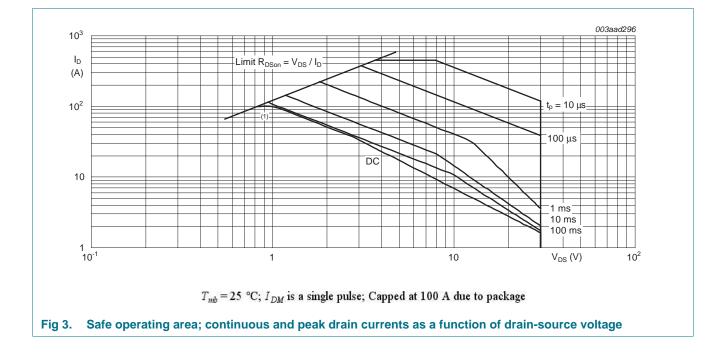






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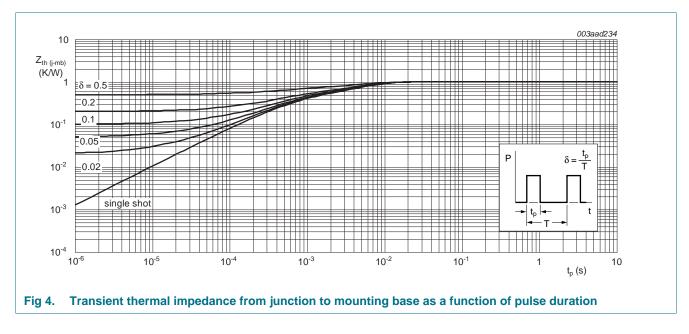
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Thermal characteristics 6.

lable 6.	I hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	1	1.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W



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Characteristics 7.

Characteristics Table 7.

Tested to JEDEC standards where applicable.

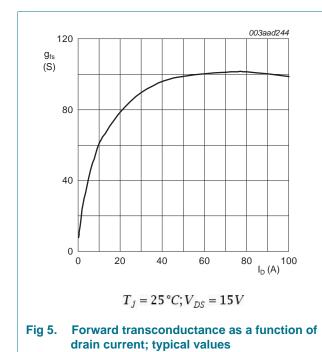
	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	40	μA
I _{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	6.65	7.8	mΩ
		V_{GS} = 4.5 V; I_D = 15 A; T_j = 25 °C; see Figure 13	-	4.46	5.2	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	4.9	5.8	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	3.5	4.1	mΩ
R _G	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic ch	haracteristics					
Q _{G(tot)}	total gate charge	I_D = 15 A; V_{DS} = 15 V; V_{GS} = 4.5 V; see Figure 14; see Figure 15	-	19	-	nC
		$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	41.5	-	nC
		$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	30	-	nC
Q _{GS}	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4	-	nC
Q _{GD}	gate-drain charge		-	5	-	nC
V _{GS(pl)}	gate-source plateau voltage	I_D = 15 A; V_{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.7	-	V
C _{iss}	input capacitance	V_{DS} = 15 V; V_{GS} = 0 V; f = 1 MHz;	-	2400	-	pF
		T _i = 25 °C; see <u>Figure 16</u>		E00		~ F
C _{oss}	output capacitance	$1 = 20^{\circ} 0,000 \frac{100000}{100000}$	-	500	-	pF

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Table 7. Characteristics ...continued

Tested to JEDEC standards where applicable.

	1	,				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; R_{L} = 0.5 Ω; V_{GS} = 10 V;	-	28	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega$	-	58	-	ns
t _{d(off)}	turn-off delay time		-	44	-	ns
t _f	fall time		-	21	-	ns
Source-dr	ain diode					
V_{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.81	1.2	V
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/μs;	-	35	-	ns
Q _r	recovered charge	$V_{GS} = 0 V; V_{DS} = 15 V$	-	30	-	nC



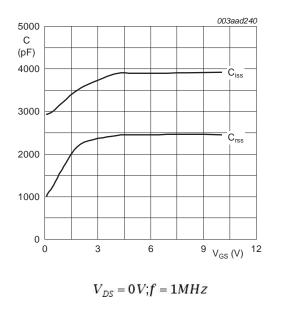
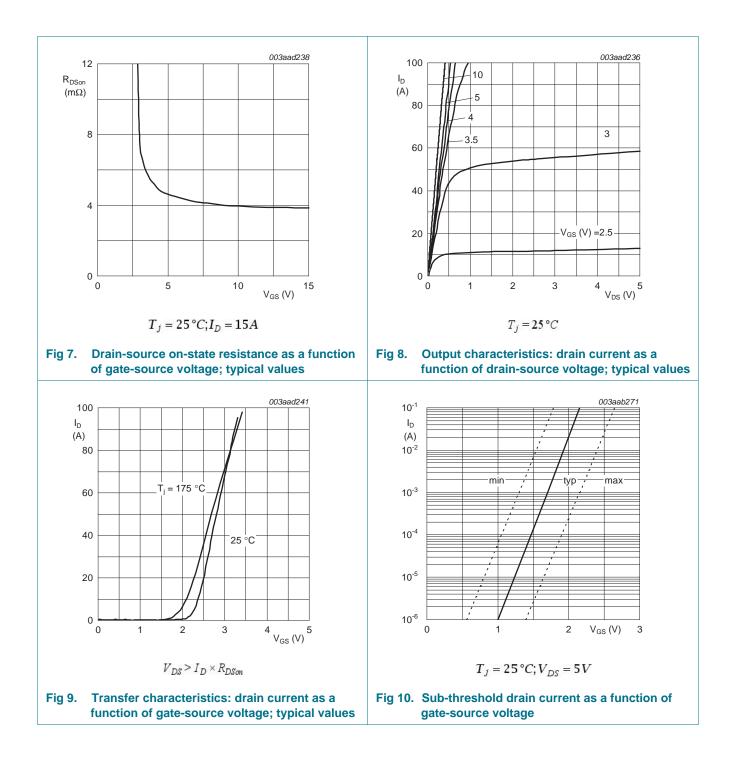


Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

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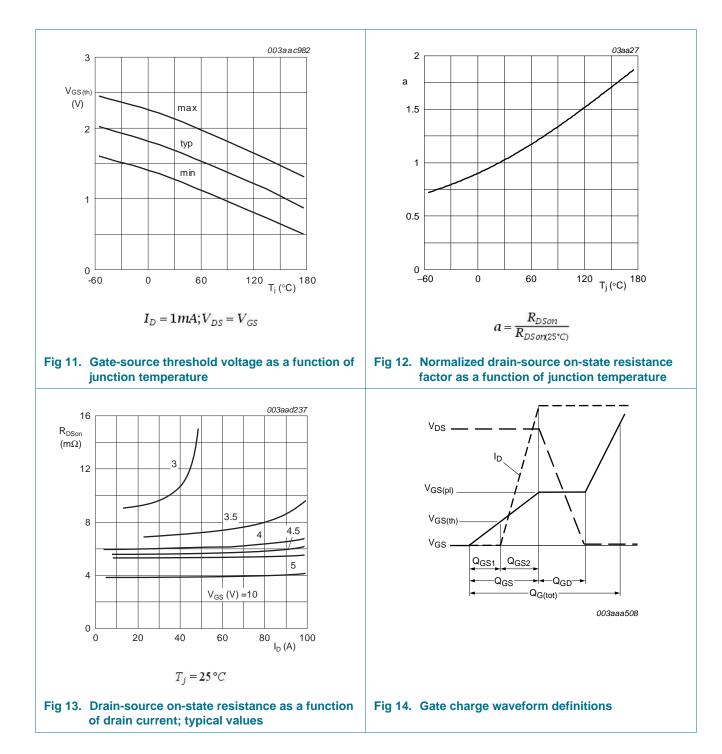


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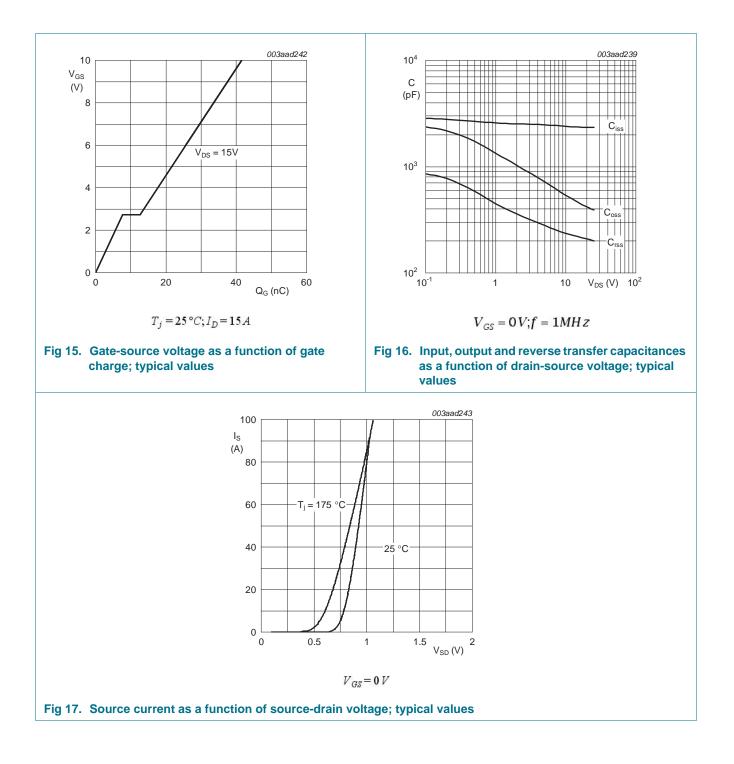
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8. Package outline

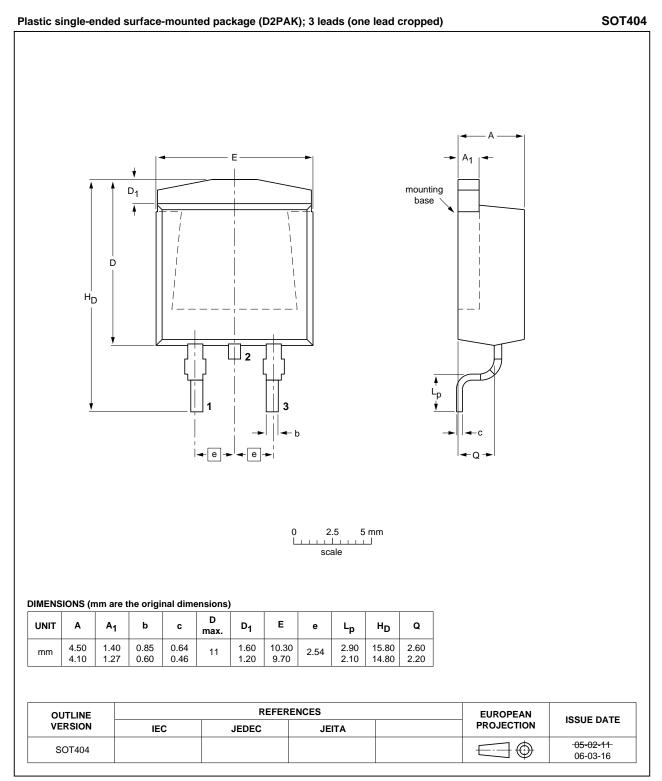


Fig 18. Package outline SOT404 (D2PAK)

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9. Revision history

Table 8. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PSMN4R3-30BL v.1	20120322	Product data sheet	-	-	

10. Legal information

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Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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